



LI DE HENG ELECTRONICS

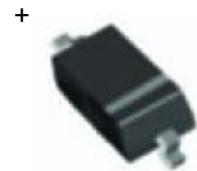
**BAT54WS**  
SOD-323 Plastic-Encapsulate Diodes

## BA T54WS Schottky Diodes

### FEATURES

- Extremely Fast Switching Speed
- Low forward voltage

SOD-323



### Maximum Ratings @ $T_A=25^\circ\text{C}$

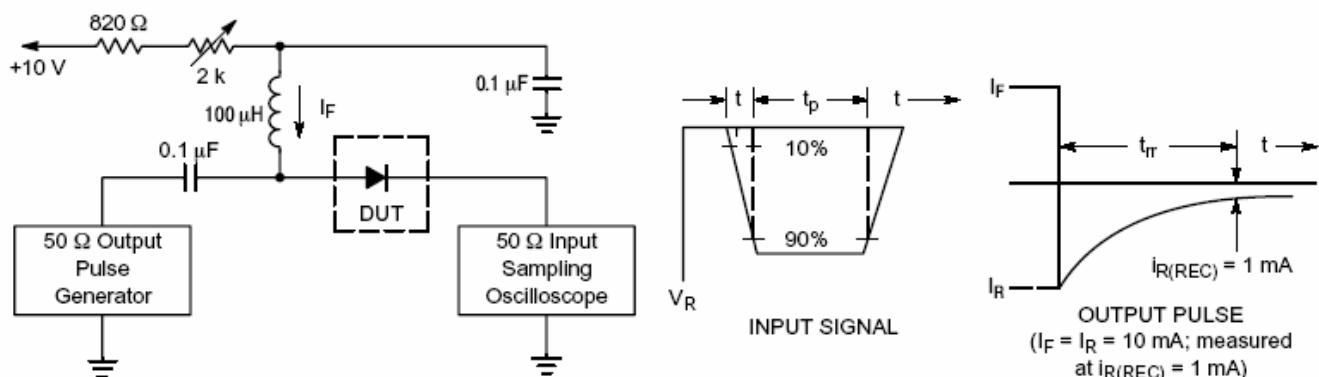
Parameter Symbol		Limits	Unit
Non-Repetitive Peak reverse voltage	$V_{RM}$	30	V
DC Blocking Voltage	$V_R$	21	V
Average Rectified Output Current	$I_O$	100	mA
Forward continuous Current	$I_F$	200	mA
Repetitive peak Forward Current	$I_{FRM}$	300	mA
Forward Surge Current	$I_{FSM}$	600	mA
Power Dissipation	$P_d$	200	mW
Thermal resistance,junction to ambient air	$R_{\theta JA}$	625	°C/W
Junction temperature	$T_J$	125	°C
Storage temperature range	$T_{STG}$	-65-150	°C

### Electrical Characteristics @ $T_A=25^\circ\text{C}$

Parameter	Symbol	Conditions	Min. T	yp.	Max.	Unit
Reverse Breakdown Voltage	$V_{(BR)R}$	$I_R=100\mu\text{A}$	30			V
Forward voltage	$V_{F1}$	$I_F=0.1\text{mA}$			240	mV
	$V_{F2}$	$I_F=1.0\text{mA}$			320	mV
	$V_{F3}$	$I_F=10\text{mA}$			400	mV
	$V_{F4}$	$I_F=30\text{mA}$			500	mV
	$V_{F5}$	$I_F=100\text{mA}$			1000	mV
Reverse current	$I_R$	$V_R=25\text{V}$			2.0	uA
Reverse recovery time	$t_{rr}$	$I_F=10\text{mA}, I_R=10\text{mA to }1\text{mA}, R_L=100\Omega$			5.0	ns
Capacitance between terminals	$C_T$	$V_R=1\text{V}, f=1\text{MHz}$			10	pF

**Typical Characteristics BAT54WS**  
LI DE HENG ELECTRONICS

1N4148WS/BAV16WS



- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current ( $I_F$ ) of 10 mA.  
 2. Input pulse is adjusted so  $I_{R(\text{peak})}$  is equal to 10 mA.  
 3.  $t_p \gg t_r$

Figure 1. Recovery Time Equivalent Test Circuit

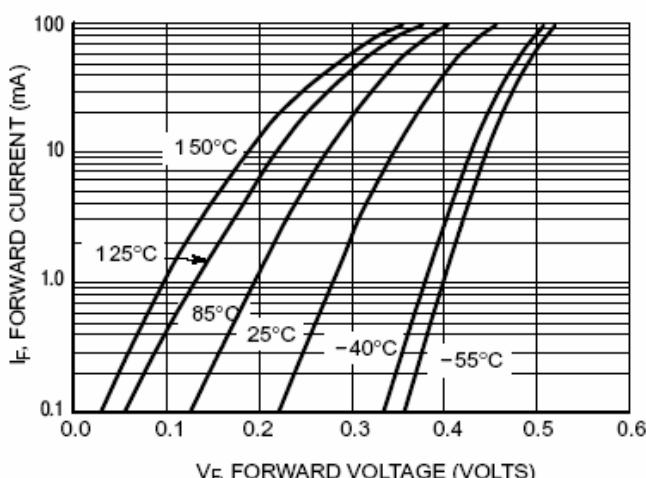


Figure 2. Forward Voltage

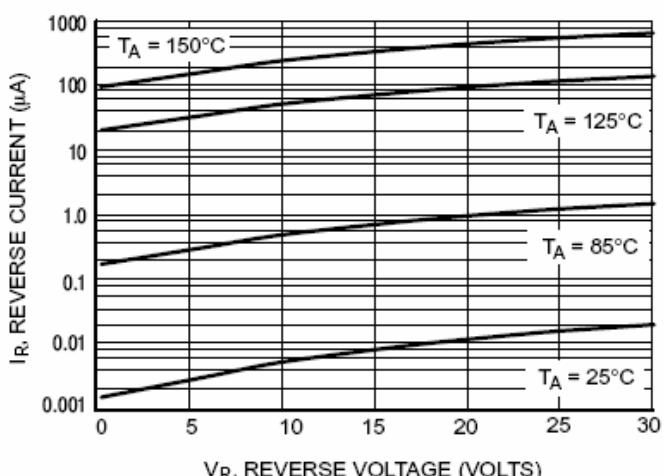


Figure 3. Leakage Current

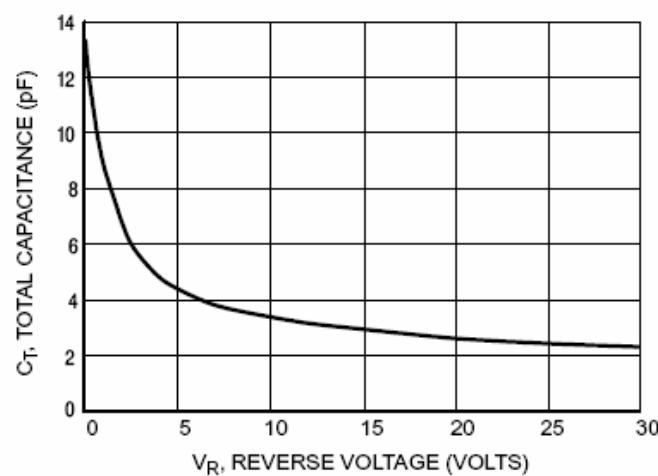


Figure 4. Total Capacitance